

# Ting Liang

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/1831509/publications.pdf>

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8  
papers

61  
citations

1684188  
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1872680  
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8  
all docs

8  
docs citations

8  
times ranked

90  
citing authors

#	ARTICLE	IF	CITATIONS
1	Oxide Thin-Film Transistors With IMO and IGZO Stacked Active Layers for UV Detection. IEEE Journal of the Electron Devices Society, 2017, 5, 504-508.	2.1	22
2	Pâ€20: Effects of N <sub>2</sub> O Plasma Treatment Time on the Performance of Self-Aligned Top-Gate amorphous oxide Thin Film Transistors. Digest of Technical Papers SID International Symposium, 2017, 48, 1299-1302.	0.3	11
3	Scalability and Stability Enhancement in Self-Aligned Top-Gate Indium- Zinc-Oxide TFTs With Al Reacted Source/Drain. IEEE Journal of the Electron Devices Society, 2018, 6, 680-684.	2.1	9
4	Homo-Junction Bottom-Gate Amorphous Inâ€Gaâ€Znâ€O TFTs With Metal-Induced Source/Drain Regions. IEEE Journal of the Electron Devices Society, 2019, 7, 52-56.	2.1	9
5	Nonlinear photocurrent-intensity behavior of amorphous InZnO thin film transistors. Applied Physics Letters, 2018, 112, .	3.3	8
6	High reliability of IGZO TFTs using low-temperature fabricated organic passivation layers. , 2016, , .		1
7	Pâ€21: The Effect of Thermal Annealing Sequence on the Performance of Self-Aligned Top-Gate â€IGZO TFTs. Digest of Technical Papers SID International Symposium, 2017, 48, 1303-1306.	0.3	1
8	Pâ€1.14: The Influence of Dual-Channel on the Performance of Self-Align Top-Gate IGZO Thin Film Transistors. Digest of Technical Papers SID International Symposium, 2018, 49, 561-564.	0.3	0